

(Applies to Mastr II, Exec II, and Custom MVP. Noise Blanker version is LBI-4991)

MAINTENANCE MANUAL

25—50 MHz RF ASSEMBLY 19D416478G1-G4 AND MIXER/IF BOARD 19C320094G1-G4

TABLE OF CONTENTS		
DESCRIPTION	Page	1
CIRCUIT ANALYSIS	Page	1
OUTLINE DIAGRAM	Page	3
SCHEMATIC DIAGRAMS		
RF Assembly	Page Page	4 5
PARTS LIST & PRODUCTION CHANGES	Page	6

DESCRIPTION

The RF Assembly uses two tuned helical resonators and four L-C tuned circuits to provide front end selectivity.

The Mixer/IF board (MIF) uses the RF input from the RF Assembly and the mixer injection frequency from the oscillator/multiplier board to generate the IF frequency.

CIRCUIT ANALYSIS

RF ASSEMBLY

ANTENNA INPUT A301

An RF signal from the antenna is applied to A301 which provides an AC ground between vehicle ground and receiver A-. Resistor R1 prevents a static charge from building up on the vehicle antenna. The output of A301 is coupled through two high-Q helical resonators (L301, C301 and L302, C302) to the RF amplifier. The coils are tuned to the incoming frequency by C301 and C302. Lamp DS1 protects the RF amplifier stage against an excessive RF input.

RF AMPLIFIER A302

RF Amplifier Ql is a Field-Effect Transistor (FET). Ql operates as a grounded gate amplifier, with the RF input applied to the "source" terminal. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through four L-C tuned circuits (L1-C7, L2-C8, L3-C9 and L4-C10) to the mixer. The four tuned circuits and the two helical resonators provide the receiver front end selectivity.

MIXER-IF

MIXER & CRYSTAL FILTER

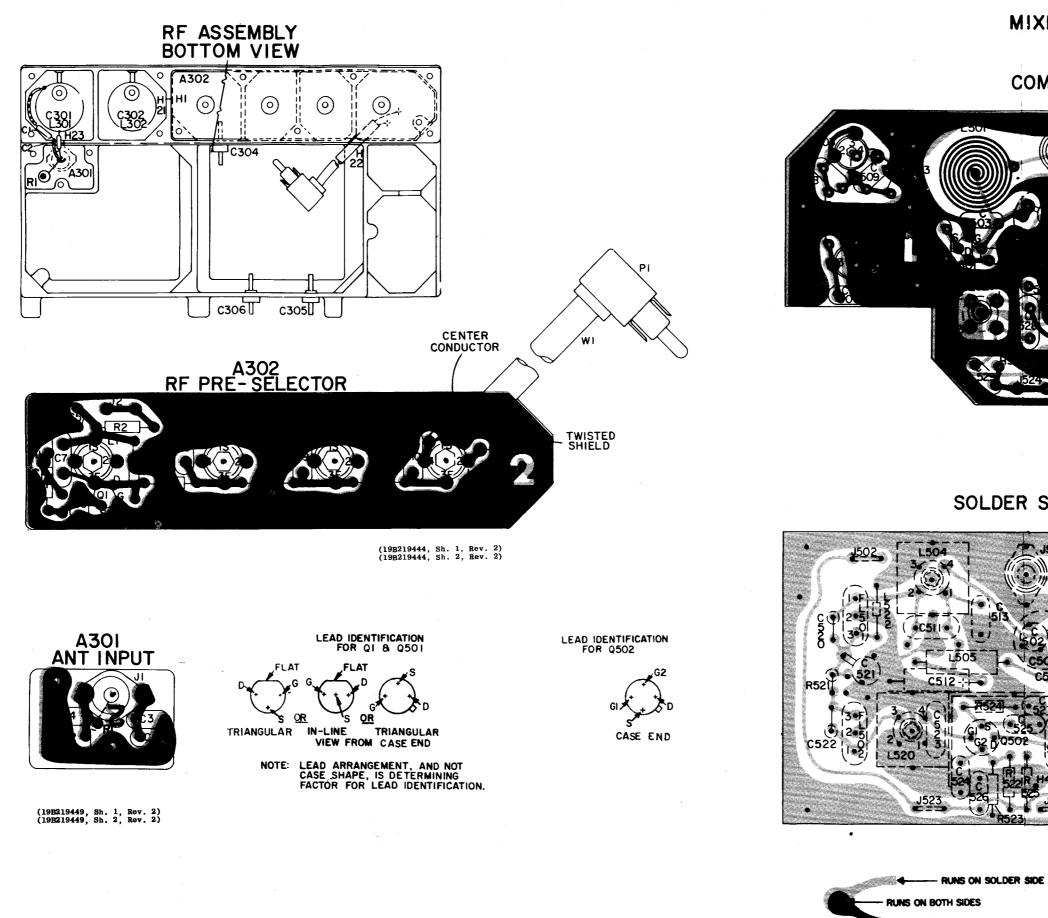
The mixer uses a FET (Q501) as the active device. The FET mixer provides a high input impedance, high power gain, and an output relatively free of harmonics (low in intermodulation products).

In the mixer stage, RF from the RF amplifier stage is coupled through tank circuit L501 and C502 to the gate of mixer Q501. The tank circuit provides increased selectivity and impedance matching between the RF Assembly and the gate of mixer Q501. Injection voltage from the multiplierselectivity stages is inductively coupled through L502 to the source of the mixer. The mixer IF output signal is coupled from the drain of Q501 through a tuned circuit (L504 and C511) which matches the mixer output to the input of the four-pole monolithic crystal filter. The highly-selective crystal filter (FL501 and FL502) provides the first portion of the receiver IF selectivity. The output of the filter is coupled through impedance matching network Z502 (L520 and C523) to the IF amplifier.

IF AMPLIFIER

IF amplifier Q502 is a dual-gate FET. The filter output is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing on Gate 2 and the drain load determines the gain of the stage. The amplifier provides approximately 20 dB of IF gain. The output of Q502 is coupled through a network (L521 and C528) that matches the amplifier output to the crystal filter on the next IF stage. The output of the MIF board is coupled to the next IF stage through feed-through capacitor C305.

Supply voltage for the RF amplifier and MIF board is supplied through feedthrough capacitor C306. <u>SERVICE NOTE</u>: Variable capacitor C521 does not require adjustment when performing normal alignment. If the 4-pole monolithic crystal filter is replaced, then adjustment of C521 is necessary for optimum IF response.



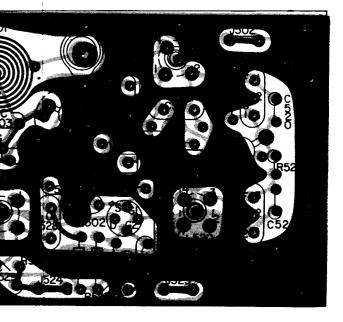
.

.

(19D423628, Rev. 2)

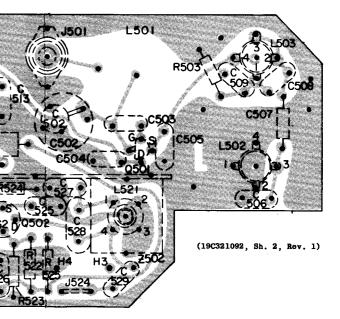
MIXER/IF BOARD

COMPONENT SIDE



(19C321092, Sh. 2, Rev. 1) (19C321092, Sh. 3, Rev. 1)

SOLDER SIDE

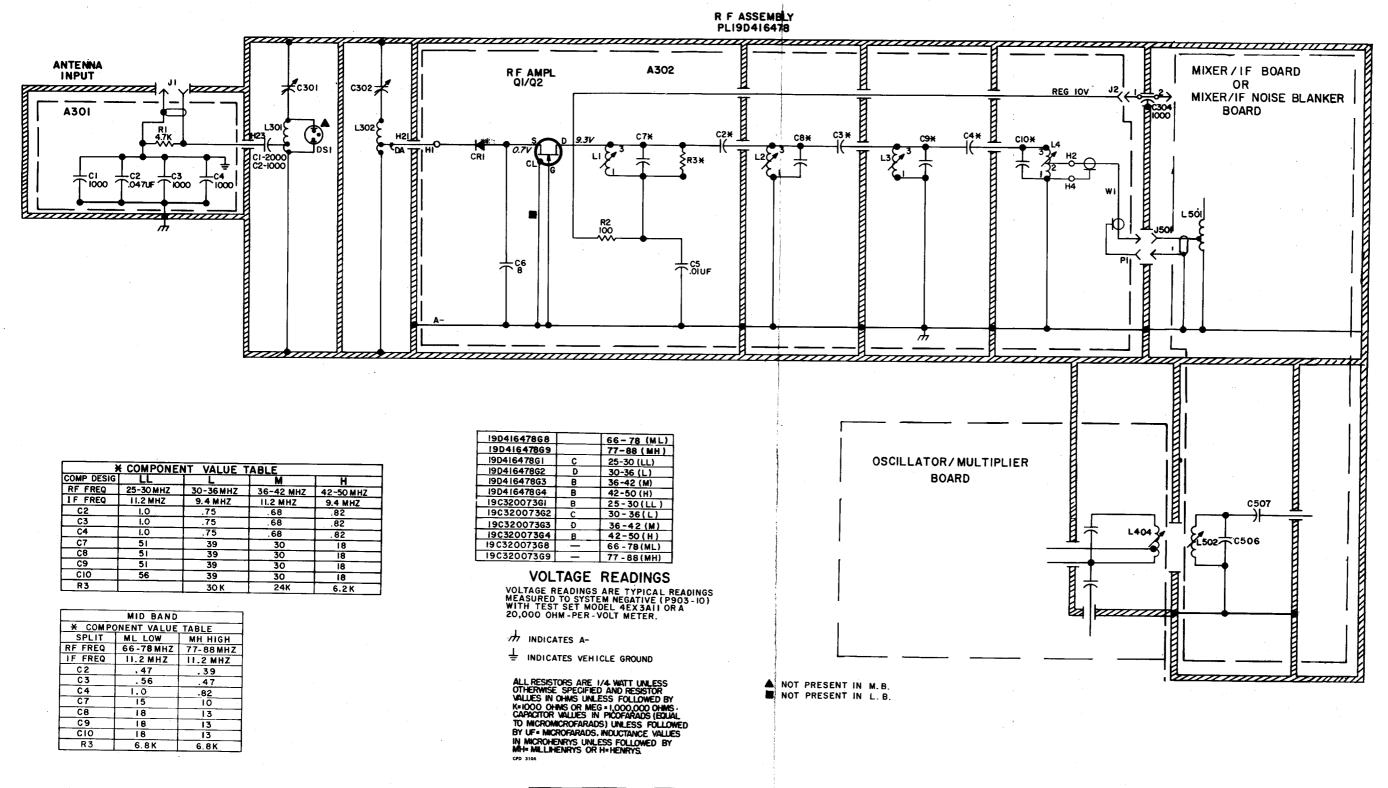


OUTLINE DIAGRAM

25-50 MHz RF ASSEMBLY AND MIXER/IF BOARD

Issue 3

RUNS ON COMPONENT SIDE



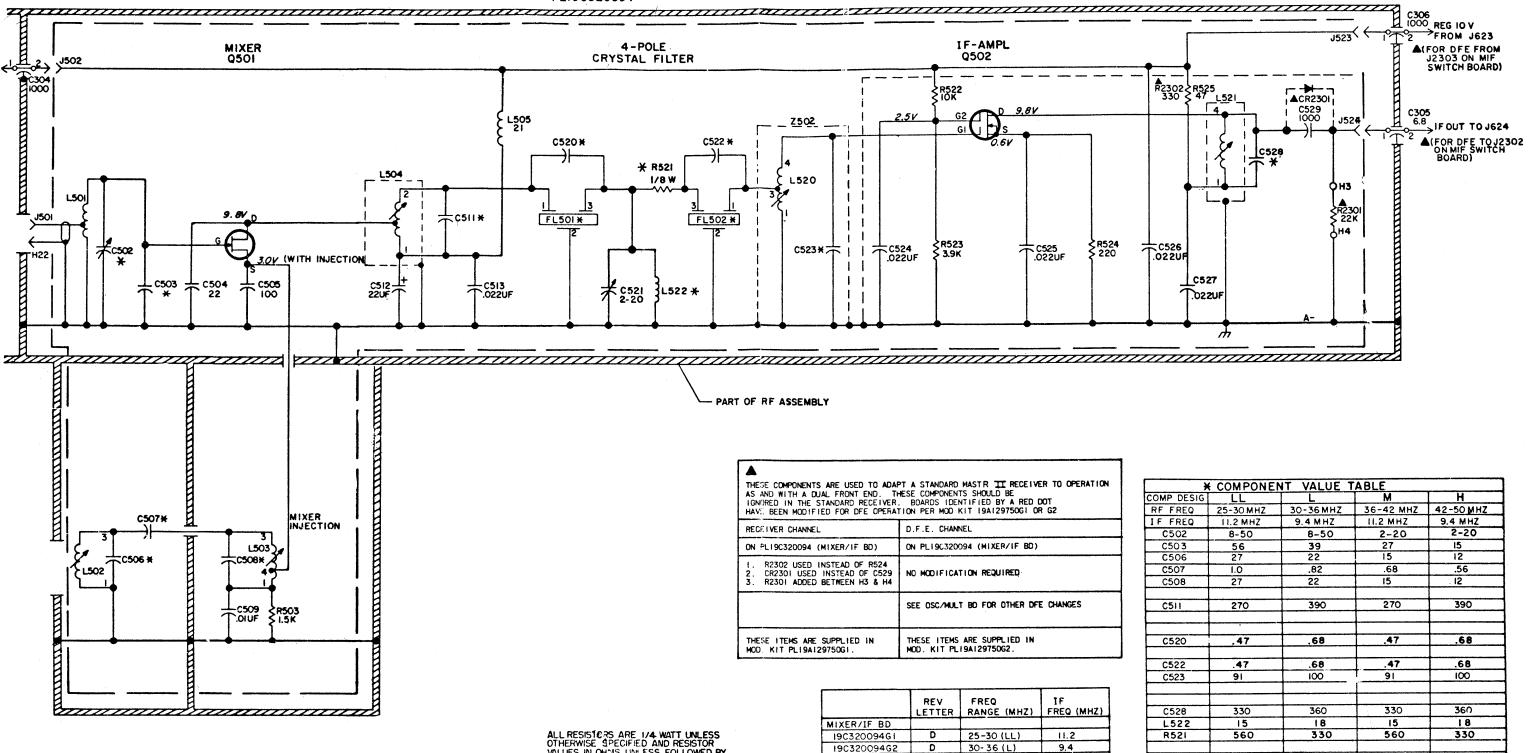
IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

SCHEMATIC DIAGRAM

25-50 MHz RF ASSEMBLY

(19D423475, Rev. 7)

MIXER/IF BD PL19C320094



19C320094G3

19C320094G4

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3AII OR A 20,000 OHM-PER-VOLT METER.



Ŧ INDICATES VEHICLE GROUND ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG = 1,000,000 OHMS -CAPACITOR VALUES : PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF . MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS. CPD 3104

> IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

11.2

9.4

36-42 (M)

42-50 (H)

С

С

			and a second	
}	COMPONEN	IT VALUE T	ABLE	
COMP DESIG	LL	L	M	Н
RF FREQ	25-30 MHZ	30-36 MHZ	36-42 MHZ	42-50 MHZ
IF FREQ	11.2 MHZ	9.4 MHZ	II.2 MHZ	9.4 MHZ
C502	8-50	8-50	2-20	2-20
C503	56	39	27	15
C506	27	22	15	12
C507	1.0	.82	.68	.56
C508	27	22	15	. 12
C511	270	390	270	390
	· ·			
C520	.47	.68	.47	.68
C522	.47	.68	.47	.68
C523	91	100	91	100
]		1
C528	330	360	330	360
L522	15	18	15	18
R521	560	330	560	330
		1		
FL501	FL50ILL	FL50IL	FL50IM	FL50IH
FL502	FL502LL	FL502L	FL502M	FL502H

SCHEMATIC DIAGRAM

25-50 MHz MIXER/IF BOARD

LBI-4989

		PARTS LIST
		LBI-4990C
	PT	25-50 MHz F ASSEMBLY 19D416478G1-G4
		F ASSEMBLY 19D416478G1-G4 AND IF ASSEMBLY 19C320094G1-G4
SYMBOL	GE PART NO.	DESCRIPTION
		RF ASSEMBLY 19D416478G1 25-30 MHz (LL)
		19D416478G2 30-36 MHz (L) 19D416478G3 36-42 MHz (M)
		19D416478G4 42-50 MHz (H)
A301		COMPONENT BOARD 19B219452C1
		19621943231
		CAPACITORS
C1	19A116655P19	Ceramic disc: 1000 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C2	19A116080P5	Polyester: 0.047 μ f ±20%, 50 VDCW.
C3 and	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C4		JACKS AND RECEPTACLES
J1	19A130924G1	
		Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613.
Rl	3R152P472K	Composition: 4.7K ohms ±10%, 1/4 w.
A302		COMPONENT BOARD
		19C320073G1 25-30 MHz (LL) 19C320073G2 30-36 MHz (L)
		19C320073G3 36-42 MHz (M) 19C320073G4 42-50 MHz (H)
		CAPACITORS
C2LL*	5491601P120	Phenolic: 1.0 pf $\pm 5\%$, 500 VDCW.
		In REV A and earlier:
	5491601P122	Phenolic: 1.2 pf $\pm 5\%$, 500 VDCW.
C2L*	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW. In REV B and earlier:
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
C2M*	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.
		In REV C and earlier:
	5491601 P 119	Phenolic: 0.82 pf $\pm 5\%$, 500 VDCW.
C2H*	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
	54016010100	In REV A and earlier:
C3LL*	5491601P120 5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW. Phenolic: 1.0 pf ±5%, 500 VDCW.
Coatta -		In REV A and earlier:
	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.
C3L*	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.
		In REV B and earlier:
C3X *	5491601P120	Phenolic: 1.0 pf $\pm 5\%$, 500 VDCW.
С3М*	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW. In REV C and earlier:
	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
сзн*	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
		In REV A and earlier:
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
C4LL*	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
	5491601P122	In REV A and earlier: Phenolic: 1.2 pf ±5%, 500 VDCW.
	2451001P122	FIGHOITC: 1.2 pr 10%, 000 then.
	1	1

SYMBOL	ge part no.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	ge part no.	DESCRIPTION	
C4L*	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.			PLUGS	L302H	19B219455G4	Coil. Includes;	C513	19A116080P3	Polyester: 0.022 µf ±20%, 50 VDCW.	L505	7488079 P 48	Choke, RF: 27.0 µh ±10%, 1.40 ohms DC res max;	
	-	In REV B and earlier:	P1		(Part of W1).	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C520LL	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.			sim to Jeffers 4422-9K.	
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.						peak; sim to EF Johnson 189.	C520L	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.	L520LL		(Part of Z502LL).	Changes are ide
C4M*	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.						MISCELLANEOUS	C520M	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.	L520L		(Part of Z502L).	number vious r
-			Ql	19A116154P1	N Type, field effect.		19B201074P305		С520Н	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.	L520M		(Part of Z502M).	fected
	F 401 (01 P110	In REV C and earlier:			RESISTORS		1982010749305	Tap screw, Phillips POZIDRIV [®] : No. 6-32 x 5/16. (Secures A301 and A302).	C521	19B209351P2	Variable: 2.5 to 20 pf, 200 VDCW, -250 +700	L520H		(Part of Z502H).	
	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.	R2	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.				0011	1000000110	PPM/°C; sim to Matshushita ECV-1ZW20P32.	L521	19C320141G6	Coil. Includes:	REV. A
C4H*	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.	R3L*	3R152P303J	Composition: 30K ohms ±5%, 1/4 w. Deleted by				C522LL	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.		5493185P9	Tuning slug.	REV. A
	5491601P120	In REV A and earlier: Phenolic: 1.0 pf ±5%, 500 VDCW.			REV B. Added to G2 by REV D.				C522L	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.	L522LL	19B209420P27	Coil, RF: 15.0 μh ±5%, 2.75 ohms DC res max; sim to Jeffers 441316-2J.	REV. A
C5	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.	₽3M*	3R152P243J	Composition: 24K ohms $\pm 5\%$, 1/4 w. Added by REV C.			MIF ASSEMBLY 19C320094G1 25-30 MHz (LL)	C522M C522H	5491601P113 5491601P117	Phenolic: 0.47 pf ±5%, 500 VDCW. Phenolic: 0.68 pf ±5%, 500 VDCW.	L522L	19B209420P28	Coil, RF: 18.0 µh ±5%, 3.00 ohms DC res max;	
C6	19A116656P8K8	Ceramic: 8 pf ±1 pf ±10%, -80 PPM.		3R152P153J	Composition: 15K ohms $\pm 5\%$, 1/4 w. Deleted by REV B.			19C320094G2 30-36 MHz (L) 19C320094G3 36-42 MHz (M) 19C320094G4 42-50 MHz (H)	C523		(Part of Z502).	L522M	19B209420P27	sim to Jeffers 441316-3J. Coil, RF: 15,0 μh ±5%, 2.75 ohms DC res max:	REV. B
C7LL	5496219P256	Ceramic disc: 51 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM.	R3H	3R152P622J	Composition: 6.2K ohms ±5%, 1/4 w.				C524 thru	19A116080P3	Polyester: 0.022 μ f ±20%, 50 VDCW.	L522H	19B209420P28	sim to Jeffers 441316-2J.	REV. C
C7L	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.				C502LL	5490446P1		C527			10220	198209420928	Cot1, RF: 18.0 µh ±5%, 3.00 ohms DC res max; sim to Jeffers 441316-3J.	
C7M	5496219P250	Ceramic disc: 30 pf $\pm 5\%$, 500 VDCW, temp coef	Wl	5491689P85	Cable, RF: approx 4 inches long. (Includes Pl).			temp coef -750 PPM; sim to Erie Style 557-36.	C528LL	5490008P139	Silver mica: 330 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.			TRANSISTORS	REV. B
С7Н	5496219P245	-80 PPM. Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef			CAPACITORS	C502L	5490446P1	Variable, ceramic: approx 8-50 pf, 350 VDCW, temp coef -750 PPM; sim to Erie Style 557-36.	C528L	5490008P40	Silver mica: 360 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	Q501	19A116154P1	N Type, field effect.	REV. C REV. D
		-80 PPM.	C301		(Part of L301).	C502M	19B209351P2	Variable, ceramic: 2.5 to 20 pf, 200 VDCW, temp coef -250 +700 PPM/°C; sim to Matshushita ECV-	C528M	5490008P139	Silver mica: 330 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	Q502	19A116818P1	N Channel, field effect.	1017.0
C8LL	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.	C302	1000000000	(Part of L302).	C502H	19B209351P2	1ZW20P32. Variable, ceramic: 2,5 to 20 pf, 200 VDCW, temp	C528H	5490008P40	Silver mica: 360 pf ±5%, 500 VDCW; sim to			RESISTORS	REV. D
C8L	5496219P253	Ceramic disc: 39 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM.	C304	19B209488P2	Ceramic, feed-thru: 1000 pf +100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.			coef -250 +700 PPM/°C; sim to Matshushita ECV- 1ZW20P32.	C529	19A116655P19	Electro Motive Type DM-15. Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	R503 R521LL	3R152P152K 3R151P561J	Composition: $1.5K$ ohms $\pm 10\%$, $1/4$ w.	
C8M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	C305	19B209488P1	Ceramic, feed-thru: 6.8 pf ±20%, 500 VDCW; sim to Allen-Bradley Style FA5D.	C503LL	5490008P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	0025	154110000115	RMC Type JF Discap.	R521LL R521L	3R151P331J	Composition: 560 ohms ±5%, 1/8 w. Composition: 330 ohms ±5%, 1/8 w.	REV. A.I
С8Н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef	C306	19B209488P2	Ceramic, feed-thru: 1000 pf +100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.	C503L	5490008P17	Silver mica: 39 pf ±5%, 500 VDCW; sim to			FILTERS	R521M	3R151P561J	Composition: 560 ohms ±5%, 1/8 w.	REV. C -
C9LL	5496219P256	-80 PPM. Ceramic disc: 51 pf $\pm 5\%$, 500 VDCW, temp coef			INDUCTORS	C503M	5490008P13	Electro Motive Type DM-15. Silver mica: 27 pf ±5%, 500 VDCW; sim to	FL501LL	19B219573G5	Crystal, freq: Sec 1: Resonator A: 11,204000 KHz,	R521H	3R151P331J	Composition: 330 ohms ±5%, 1/8 w.	
C9L	5496219P253	-80 PPM. Ceramic disc: 39 pf $\pm 5\%$, 500 VDCW, temp coef	L301LL	19B219455G1	Coil. Includes:	С503н	5490008P8	Electro Motive Type DM-15. Silver mica: 15 pf ±5%, 500 VDCW; sim to			Resonator B: 11,196000 KHz. Sec 2: Resonator A: 11,204000 KHz.	R522 R523	3R152P103K 3R152P392K	Composition: 10K ohms ±10%, 1/4 w. Composition: 3.9K ohms ±10%, 1/4 w.	
0.91	54502157255	-80 PPM.	C1*	5494481P13	Capacitor, ceramic disc: 2000 pf ±20%, 1000	COOSH	349000828	Electro Motive Type DM-15.			Resonator B: 11,196000 KHz.	R524	3R152P221K	Composition: 220 ohms ±10%, 1/4 w.	
СЭМ	5496219P250	Ceramic disc: 30 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM.			VDCW; sim to RMC Type JF Discap. In 19D416478G2 of REV B and earlier:	C504	19A116656P22J0	Ceramic disc: 22 pf $\pm 5\%$, 500 VDCW, temp coef 0 PPM.	FL501L	19B219574G3	Crystal, freq: Sec 1: Resonator A: 11,200000 KHz, Resonator B: 11,196024 KHz.	R525	3R152P470K	Composition: 47 ohms ±10%, 1/4 w.	
СЭН	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.		5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000	C505	5490008 P 27	Silver mica: 100 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.			Sec 2: Resonator A: 11,200000 KHz, Resonator B: 11,196024 KHz.				
C10LL	5496219P257	Ceramic disc: 56 pf \pm 5%, 500 VDCW, temp coef	C301	19B209159P4	VDCW; sim to RMC Type JF Discap. Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C506LL	19A116656P27K8	Ceramic disc: 27 pf ±10%, 500 VDCW, temp coef	FL501M	19B219573G5	Crystal, freq: Sec 1: Resonator A: 11,204000 KHz.	Z502LL	19C320141G4	Coil. Includes:	
C10L	5496219P253	-80 PPM. Ceramic disc: 39 pf $\pm 5\%$, 500 VDCW, temp coef	DS1	1000000000	peak; sim to EF Johnson 189.	C506L	19A116656P24K8	-80 PPM. Ceramic disc: 24 pf ±10%, 500 VDCW, temp coef			Resonator B: 11,196000 KHz. Sec 2: Resonator A: 11,204000 KHz,		5493185P9	Tuning slug.	
		-80 PPM.	L301L	19B209067P1 19B219455G1	Lamp, glow: 0.7 ma; sim to GE NE2ET. Coil. Includes:			-80 PPM.	FL501H	19B219574G3	Resonator B: 11,196000 KHz. Crystal, freq:	Z502L	19C320141G5 5493185P9	Coil. Includes:	
C10M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	C1	5494481P13	Capacitor, ceramic disc: 2000 pf ±20%, 1000	C506M	19A116656P15K8	Ceramic disc: 15 pf ±10%, 500 VDCW, temp coef -80 PPM.			Sec 1: Resonator A: 11,200000 KHz, Resonator B: 11,196024 KHz,	Z502M	19C320141G4	Tuning slug.	
С10Н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef			VDCW; sim to RMC Type JF Discap.	С506Н	19A116656P12K8	Ceramic disc: 12 pf ±10%, 500 VDCW, temp coef			Sec 2: Resonator A: 11,200000 KHz,	2302m		Coil. Includes:	
		-80 PPM.	C301	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v			-80 PPM.	TI FORT		Resonator B: 11,196024 KHz.		5493185P9	Tuning slug.	
		DIODES AND RECTIFIERS			peak; sim to EF Johnson 189.	C507LL	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.	FL502LL		(Part of FL501LL).	Z502H	19C320141G5	Coil. Includes:	
CR1	19A116052P2	Silicon.	DS1	19B209067P1	Lamp, glow: 0.7 ma; sim to GE NE2ET.	C507L	5491601 P 119	Phenolic: 0.82 pf ±5%, 500 VDCW.	FL502L		(Part of FL501L).		5493185P9	Tuning slug.	
Chr	ISATIOUSEE	biiteon.	L301M	19B219455G3	Coil. Includes:	C507M	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.	FL502M		(Part of FL501M).				
	1	JACKS AND RECEPTACLES	C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C507H	5491601 P 115	Phenolic: 0.56 pf ±5%, 500 VDCW.	FL502H		(Part of FL501H).		19B219470P2	Shield.	
J2	19A116975P1	Receptacle, wire spring.	C301	19B209159 P 4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C508LL	19A116656P27K8	Ceramic disc: 27 pf ±10%, 500 VDCW, temp coef			JACKS AND RECEPTACLES		19821947092 198129424G1	Can. (Quantity 3).	
		INDUCTORS	DS1	19B209067P1	peak; sim to EF Johnson 189. Lamp, glow: 0.7 ma; sim to GE NE2ET.	C508L	19A116656P24K8	-80 PPM. Ceramic disc: 24 pf ±10%, 500 VDCW, temp coef	J501	19A130924G1	Receptacle, coaxial: jack type; sim to Cinch		4031594P1	Insulator. (Used with C502, C521).	
L1*	19C307170P306	Coil, RF: variable; sim to Paul Smith 092574-	L301H					-80 PPM.	TECO	10411605571	14H11613.		4035306P23	Washer, fiber. (Used with J501).	
thru L3*		DS-3.		19B219455G3	Coil. Includes:	C508M	19A116656P15K8	Ceramic disc: 15 pf ±10%, 500 VDCW, temp coef -80 PPM.	J502	19A116975P1	Receptacle, wire spring.			, , , , , , , , , , , , , , , , , , , ,	
		In 19C320073G1 REV A and earlier: In 19C320073G2 REV B and earlier:	C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	С508Н	19A116656P12K8	Ceramic disc: 12 pf ±10%, 500 VDCW, temp coef	J523 and J524	19A116975P1	Receptacle, wire spring.				
		In 19C320073G3 REV C and earlier: In 19C320073G4 REV A and earlier:	C301	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	C509	19A116080P101	-80 PPM. Polyester: 0.01 μf ±10%, 50 VDCW.							
	19B219419G2	Coil. Includes:	DS1	19B209067P1	Lamp, glow: 0.7 ma; sim to GE NE2ET.	C511	5490008P137	Silver mica: 270 pf ±10%, 500 VDCW; sim to	L501		(Part of printed board 19C321092P1).				
	5491798P5	Tuning slug.	L302LL	19B219455G2	Coil. Includes:		510000107	Electro Motive Type DM-15.	L502	19B219419G2	Coil. Includes:				
L4*	19C307170P308	Coil, RF: variable; sim to Paul Smith 071774- OG-7.	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	C511L	5490008P141	Silver mica: 390 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.		5491798P5	Tuning slug.				
		In 19C320073G1 REV A and earlier: In 19C320073G2 REV B and earlier;	L302L	19B219455G2	Coil. Includes:	C511M	5490008 P 137	Silver mica: 270 pf ±10%, 500 VDCW; sim to	L503	19B219419G4	Coil. Includes:				
		In 19082000 ABT Court earlier:	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v			Electro Motive Type DM-15.		5491798 P 5	Tuning slug.				
		In 19C320073G4 REV A and earlier:			peak; sim to EF Johnson 189.	C511H	5490008 P 141	Silver mica: 390 pf $\pm 10\%$, 500 VDCW; sim to Electro Motive Type DM-15.	L504	19C320141G30	Coil. Includes:				
	19B219419G1	Coil. Includes:	L302M	19B219455G4	Coil. Includes:	C512	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague		5493185P12	Tuning slug.				
	5491798P5	Tuning slug.	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.			Type 150D.							
		1													
		1					1			1				1	

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

ipment to improve performance or to simplify circuits
a "Revision Letter", which is stamped after the model
Refer to the Parts List for descriptions of parts afrevisions.

xer/IF Board 19C320094G1,2
xer/IF Board 19C320094G3,4
Filter Board 19C320073G1-4
ove revisions incorporated in initial
ipment.
Filter Board 19C320073G2 & 3
improve receiver sensitivity.
eted R3L and R3M.
Filter Board 19C320073G2
Filter Board 19C320073G3
improve receiver sensitivity.
nged C2, C3 and C4 and L1 thru L4.
Filter Board 19C320073G2
prevent oscillation in pre-selector board.
et R3L.
Assembly 19D416478G1-4
orporated in initial shipment.

Assembly 19D416478G1. Improve sensitivity in 25-30 MHz range. nged C1 (part of L301).

.